

In the Claims:

1-21 (canceled)

22 (currently amended) A method for etching one or more of the following: TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps of:

forming a solution by combining HF with a concentration of about 49% with H₂O₂ with a concentration of from about 29% to about 30% in deionized water (DIW), said solution having of a volume ratio of HF:H₂O₂:DIW selected from the group consisting of from about 2:1:21, 3:2:10, 3:1:10, greater than 1:1:20 and 1:1:30; and

applying said solution to said semiconductor body with said solution being at at least about room temperature.

23 (canceled)

24 (previously presented) A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps of:

forming a solution by combining HF with a concentration of about 49% with H₂O₂ with a concentration of about 30% in deionized water, said forming a solution further consisting of a volume ratio of about 2 parts HF, about 1 part H₂O₂ and about 21 parts deionized water; and

applying said solution to said semiconductor body with said solution being at about room temperature.

25 (previously presented) The method of claim 22 wherein said method further comprises applying said solution in the presence of photoresist.

26. (currently amended) A method for etching TaN₅ from a semiconductor body in semiconductor device processing, comprising the steps of:

forming a solution by combining HF with a concentration of about 49% with H₂O₂ with a concentration of about 29 to about 30% in deionized water wherein said forming a solution further consists of using a volume ratio greater than ~~of about~~ 1 part HF, ~~about~~ 1 part H₂O₂ and ~~about~~ 20 parts deionized water; and

applying said solution to said semiconductor body with said solution being at a temperature of 40°C to 50°C.

27 (canceled)

28. (previously presented) A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps of:

forming a solution by combining HF with a concentration of about 49% with H₂O₂ with a concentration of about 30% in deionized water wherein said forming a solution further consists of using a volume ration of about 2 part HF, about 1 part H₂O₂ and about 21 parts deionized water; and

applying said solution to said semiconductor body with said solution being at a temperature of from about 40°C to about 50°C.

29. (previously presented) The method of claim 26 wherein said method further comprises applying said solution in the presence of photoresist.

30. (previously presented) The method of claim 28 wherein said method further comprises applying said solution in the presence of photoresist.

31. (previously presented) The method of claim 24 wherein said method further comprises applying said solution in the presence of photoresist.